

**Federal Agency on Technical Regulating and Metrology
(Rostekhnregulirovanie)**

CENTER FOR SURFACE AND VACUUM RESEARCH

**Diffusion Length Measurement System of Minority
Charge Carriers in Silicon Wafers**

Quality control of initial silicon wafers by measurements of diffusion length of minority charge carriers and iron contamination, using a contactless, real-time surface photovoltage method.



Specifications

Measuring range:

Diffusion Length (L_D) 10 μm to 2000 μm or $L_D < t$
(t is the wafer thickness)

Iron concentration $10^9 \div 10^{13} \text{ cm}^{-3}$

Accuracy of measurements 15 \div 30 %

40 Novatorov str.

119421, Moscow, Russia

Ph.: (007-095) 935-9777

Ph./Fax: (007-095) 935-9690

E-mail fgupnicpv@mail.ru